

Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No. NOVLP097/ NVLS-2906 Applicant: Wu et al. Filing Date March 23, 2004	Application No.: 10/807,680 Group 2812 1792
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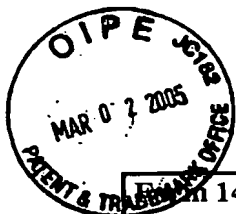
Examiner Initial	No.	Publication/ Patent No.	Date	Patentee	Class	Sub-class	Filing Date
/MLP/	A1	6,329,017	12/11/01	Liu et al.	X	X	10/04/99
	A2	6,383,466	5/7/02	Domansky et al.			12/28/98
	A3	6,365,266	4/2/02	MacDougall et al.			03/03/00
	A4	5,504,042	4/2/96	Cho et al.			06/23/94
	A5	5,858,457	1/12/96	Brinker et al.			09/25/97
	A6	6,270,846	8/7/01	Brinker et al.			03/02/00
	A7	6,387,453	5/14/02	Brinker et al.			03/02/00
	A8	6,420,441	10/10/99	Allen et al.			12/10/99
	A9	6,271,273	10/10/00	You et al.			10/10/00
	A10	20040096672	05/20/04	Lukas et al.			11/14/02
/MLP/	A11	6,444,715	09/03/02	Mukherjee, et al.			06/06/00

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*11/13/07 /MLP/	A12	Humayun et al., "Method For Forming Porous Films By Porogen Removal Combined With In Situ Surface Modification" , U.S. Application No. 10/404,693, filed March 31, 2003.
*4/24/06	A13	Cho et al., "Method And Apparatus For UV Exposure Of Low Dielectric Constant Materials For Porogen Removal And Improved Mechanical Properties" , U.S. Patent Application No. 10/800,377, filed March 11, 2004
*4/30/07	A14	Bandyopadhyay et al., "Method to Improve Mechanical Strength of Low K Dielectric Film Using Modulated UV Exposure" , U.S. Patent Application No. 10/825,888, filed April 16, 2004
*2/27/06 /MLP/	A15	Tipton et al., "Method Of Porogen Removal From Porous Low K Films Using UV Radiation" , U.S. Patent Application No. 10/672,311, filed September 26, 2003
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* applications reviewed with respect to other IDSs as indicated by date.



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	B4	5,686,054	11/11/97	Barthel et al.			05/16/95
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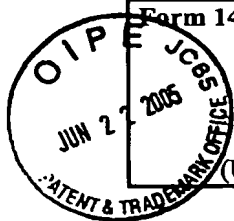
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/MLP/	C4	Justin F. Gaynor, " In-Situ Treatment of Low-K Films With a Silylating Agent After Exposure To Oxidizing Environments, " U.S. Patent Application No.10/056,926 filed January 24, 2002, 34 Pages abandon
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++ "HMDS/Supercritical Carbon Dioxide Treatment of Plasma Damaged Nanoporous Low k Films"

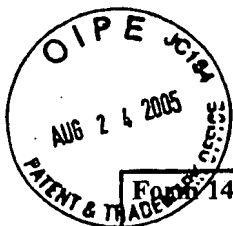


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/MLP/	C2	U.S. Office Action mailed July 27, 2005, from U.S. Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875]. also cited in 7/25/06 IDS
		both applications cited in the IDS of 2/27/2006
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/Marianne L. Padgett/	11/16/2007	

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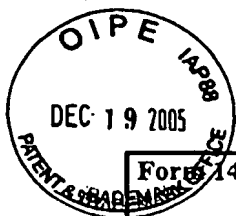
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		both applications are also cited in the IDS of 11/13/2006
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/MLP/	C1	Cho et al., "Method for Porogen Removal and Mechanical Strength Enhancement of Low-K Carbon Doped Silicon Oxide Using Low Thermal Budget Microwave Curing", U.S. Application No. 11/280,113, filed November 15, 2005 (Atty Dkt. NOVLP145/NVLS-3106)
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	C3	U.S. Office Action mailed February 7, 2006, from U.S. Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-000821]. abandoned & cited 11/13/06 IDS	
	C4	U.S. Office Action mailed December 20, 2005, from U.S. Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-000820].	
	C5	U.S. Office Action mailed December 20, 2005, from U.S. Application No. 10/849,568 [Atty Dkt No. NOVLP083/NVLS-2867]. applications cited in 7/25/06 IDS	
/MLP/	C6	U.S. Office Action mailed January 9, 2006, from U.S. Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875].	
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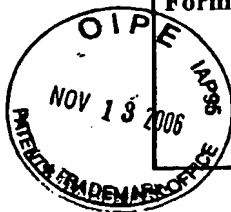
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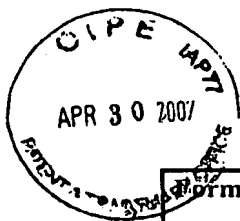
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Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No.	NOVLP097/NVLS-2906
	Application No.:	10/807,680
	Applicant	Wu et al.
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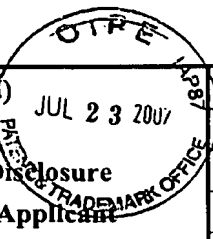
Examiner Initial		Document No.	Publication Date	Country or Patent Office	Class	Sub-Class	Translation	
							Yes	No
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Form 1449 (Modified)

Information Disclosure
Statement By Applicant

(Use Several Sheets if Necessary)

Atty Docket No.	NOVLP097/NVLS-2906
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Note office actions are not published & inappropriate for listing, however such citations are being considered citations at the application, but only one citation is needed, thus 'duplicates' on the same IDS are crossed-out.

Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No.	Application No.:
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** "Fine-Pattern Lithography for Large Substrates Using a Holographicmask-Aligner (revised edition)"

*** "Efficient Pore Sealing Crucial for Future Interconnects"

Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No.	Application No.:
	NOVLP097/ NVLS-2906	10/807,680
	Applicant:	
	Wu et al.	
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